



USB Flash / EPROM Programmer

<https://usbflashprog.robsonmartins.com>

Specifications

Version 0.2

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History

Revision	Date	Changes
0.2	Jan. 14, 2024	Created new opcodes for device programming.
	Jan. 03, 2024	Added device algorithm: Electrically Erasable EPROM.
	Jan. 02, 2024	Added device algorithm: EPROM.
	Dec. 22, 2023	New release started.
0.1 G	Dec. 19, 2023	Added device algorithm: SRAM.
	Nov. 17, 2023	Removed "run by script" requirement. Removed the external power source.
0.1 F	May. 30, 2022	Added serial communication protocol (opcodes).
0.1 E	Apr. 23, 2022	CPU changed to Raspberry Pi Pico. Updated diagrams. Removed PT_BR translation.
0.1 D	Feb. 02, 2011	Added firmware project.
0.1 C	Dec. 27, 2010	Added adapter connectors pin-out.
0.1 B	Mar. 03, 2010	New Block Diagram.
0.1 A	Jan. 28, 2010	Initial Version.

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1. Introduction

The purpose of this board is to allow the programming, reading and verification of writable/rewritable memory devices, such as EPROM, EEPROM, Flash, SRAM, NVRAM – those with parallel bus as well as serial ones (I2C, SPI, Microwire, LPC).

In a future release, programming of some microcontroller families (eg. Microchip PIC, or 8051) may also be supported, via firmware and software upgrade.

2. Requirements

- Allow write, read, delete, get ID and information about supported chips.
- Support parallel and serial devices (no microcontrollers in initial version).
- Support SRAM, EPROM, E2PROM, Flash, NVRAM, Hub/LPC devices (parallel and serial, including Microwire, I2C, SPI).
- Provide two sources of programming voltage: VDD (low voltage) and VPP/VEE (high voltage for write/erase), in the range between 3.3 V and 6.8 V (VDD), and between 12V and 25V (VPP/VEE).
- Automatic control for VDD and VPP/VEE voltages, according to the chip to be programmed.
- Allow *jumperless* chip configuration (by software chip selection).
- Socket for adapters – for each package or family of supported chips (no ZIF socket on the programmer board).
- Connection with PC via USB port, using a specific software for communication.
- Multi-platform software, compatible with Microsoft Windows® or GNU/Linux® operating systems, under 32 or 64 bits (if possible, Apple macOS® and FreeBSD versions can be available).
- Some compatibility with existing programmers adapters:
 - EzoFlash+ (<http://www.ezoflash.com/>).
 - MPSP (<https://mpsp.robsonmartins.com>).

3. Hardware Platform

3.1. Block Diagram

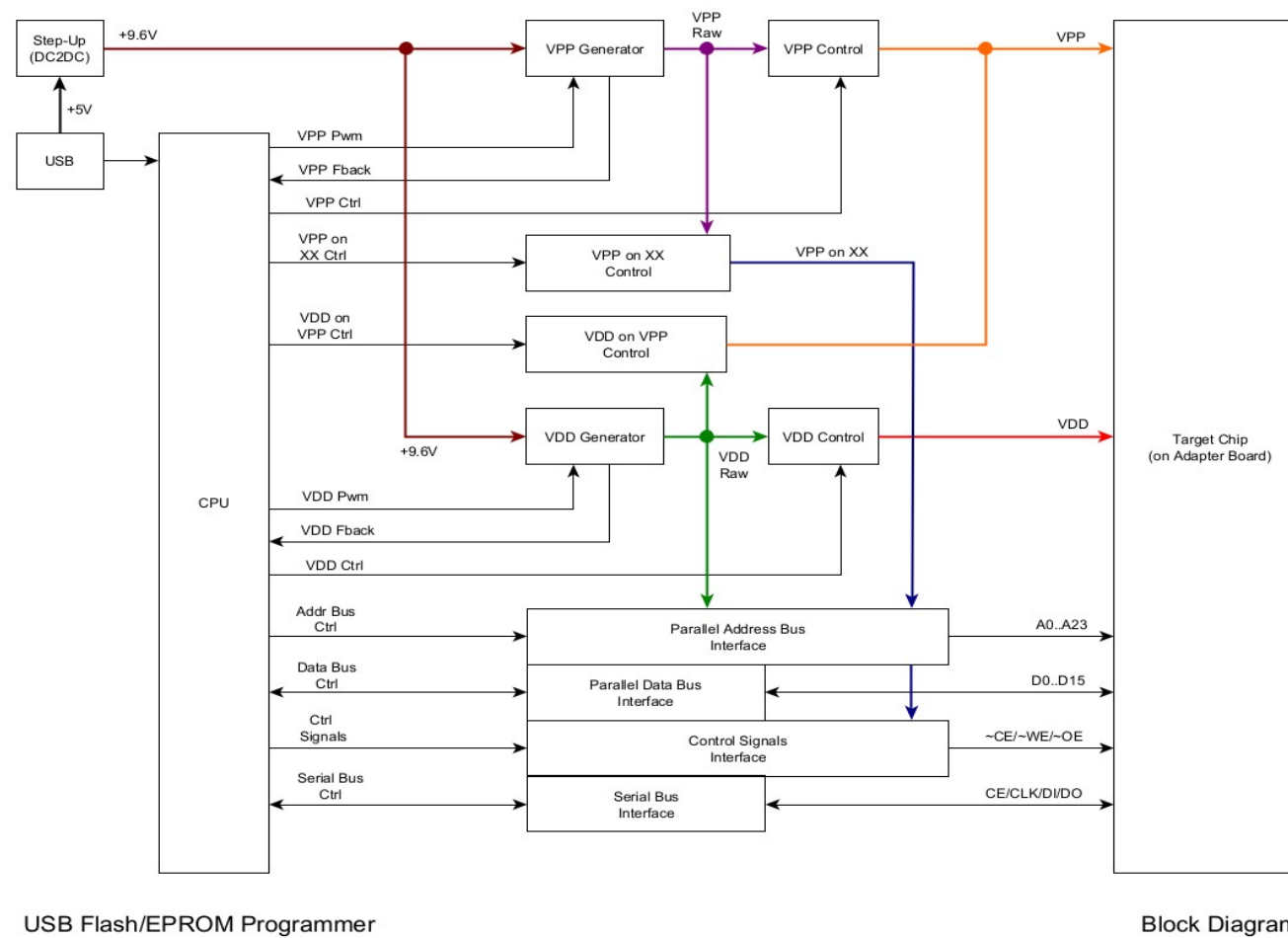


Figure 1: USB Flash/EPROM Programmer Block Diagram

3.2. Functional Description

3.2.1. Main CPU

The CPU used in this programmer will be a Raspberry Pi Pico Module (with a RP2040 processor and USB support). This module has a dual core ARM Cortex-M0+ running at 133MHz, 256KB of SRAM and 2MB of storage, a USB port, required for communication between the programmer and the PC, plus one A/D converter with 3 inputs and 16 PWM channels (that can be used to generate the programming voltages). Moreover, there is a serial communication port (SPI / Microwire / I2C) that can be used for programming of serial devices, and GPIO pins to control parallel bus and signals.

3.2.2. Power Supplies

To generate the programming voltages (VDD and VPP/VEE), the programmer must have two DC/DC converters, driven by the PWM outputs of the CPU and monitored through of the ADC inputs.

The CPU will be powered directly by the voltage supplied by the USB port (5V). A fixed DC/DC converter will step up the voltage to 9.6V, to power the two DC/DC converters – VDD and VPP/VEE generators.

The CPU can turn on or off the VDD / VPP / VEE outputs, or supply VDD voltage on VPP line (via the “VDD on VPP” signal).

3.2.3. Programmer Busses

For handle parallel devices, the programmer must provide the following busses and signals to the target chip:

- **Address Bus (A0..A23)** – A addressing bus with 24 bits wide, allowing access up to 16777216 positions (16M).
- **Data Bus (D0..D7 / D8..D15)** – A data bus with 8 or 16 bits wide, allowing access for one byte (8 bits) or one word (16 bits), according to the memory width.
- **Control Lines (~CE / ~WE / ~OE)** – Chip Enable, Write Enable e Output Enable.
- **Power and Programming Voltages (VDD / VPP / VEE)** - Voltages used to power-up (VDD), program (VPP) or erase (VEE) the memory.

For handle serial devices, the programmer must provide the following signals to the target chip:

- **Clock (CLK)** – Clock line for synchronize the communication with the target memory.
- **Data Input (DIN)** – For read data from target memory.
- **Data Output (DOUT)** – For write data to target memory.

- **Control Lines (\sim CE / \sim WE / \sim OE)** – Chip Enable, Write Enable e Output Enable.
- **Power and Programming Voltages (VDD / VPP / VEE)** - Voltages used to power-up (VDD), program (VPP) or erase (VEE) the memory.

3.2.4. Busses Interfaces

To connect the microcontroller busses to target chip, is necessary adapt the voltage levels of the CPU (5V) and the voltage levels of the target chip ($3.3V \leq VDD \leq 6.8V$), using an interface circuitry.

3.3. Adapter Connector Pin-Out

3.3.1. Parallel Adapter Connector

Female (Top Side)

1	3	5	7	9	11	13	15	17	19	21	23	25	27	29	31	33	35	37	39	41	43	45	47
2	4	6	8	10	12	14	16	18	20	22	24	26	28	30	32	34	36	38	40	42	44	46	48

Table 1: Parallel Adapter Connector Pin-Out

Pin	Function	Description
1	D0	DATA BUS – BIT 0
2	D1	DATA BUS – BIT 1
3	D2	DATA BUS – BIT 2
4	GND	GROUND
5	D3	DATA BUS – BIT 3
6	D4	DATA BUS – BIT 4
7	D5	DATA BUS – BIT 5
8	D6	DATA BUS – BIT 6
9	D7	DATA BUS – BIT 7
10	$\overline{\text{CE}}$	CHIP ENABLE
11	A10	ADDRESS BUS – BIT 10
12	$\overline{\text{OE}}$	OUTPUT ENABLE
13	A11	ADDRESS BUS – BIT 11
14	A9	ADDRESS BUS – BIT 9
15	A8	ADDRESS BUS – BIT 8
16	A13	ADDRESS BUS – BIT 13
17	A14	ADDRESS BUS – BIT 14
18	A17	ADDRESS BUS – BIT 17
19	$\overline{\text{WE}}$	WRITE ENABLE

Pin	Function	Description
20	VDD	VDD VOLTAGE
21	A18	ADDRESS BUS – BIT 18
22	A16	ADDRESS BUS – BIT 16
23	A15	ADDRESS BUS – BIT 15
24	A12	ADDRESS BUS – BIT 12
25	A7	ADDRESS BUS – BIT 7
26	A6	ADDRESS BUS – BIT 6
27	A5	ADDRESS BUS – BIT 5
28	A4	ADDRESS BUS – BIT 4
29	A3	ADDRESS BUS – BIT 3
30	A2	ADDRESS BUS – BIT 2
31	A1	ADDRESS BUS – BIT 1
32	A0	ADDRESS BUS – BIT 0
33	KEY	KEY TO AVOID CONNECTOR INVERSION
34	VPP	VPP PROGRAMMING VOLTAGE
35	A19	ADDRESS BUS – BIT 19
36	A20	ADDRESS BUS – BIT 20
37	A21	ADDRESS BUS – BIT 21
38	A22	ADDRESS BUS – BIT 22
39	A23	ADDRESS BUS – BIT 23
40	KEY	KEY TO AVOID CONNECTOR INVERSION
41	D8	DATA BUS – BIT 8
42	D9	DATA BUS – BIT 9
43	D10	DATA BUS – BIT 10
44	D11	DATA BUS – BIT 11
45	D12	DATA BUS – BIT 12
46	D13	DATA BUS – BIT 13
47	D14	DATA BUS – BIT 14
48	D15	DATA BUS – BIT 15

3.3.2. Serial Adapter Connector

Female (Top Side)

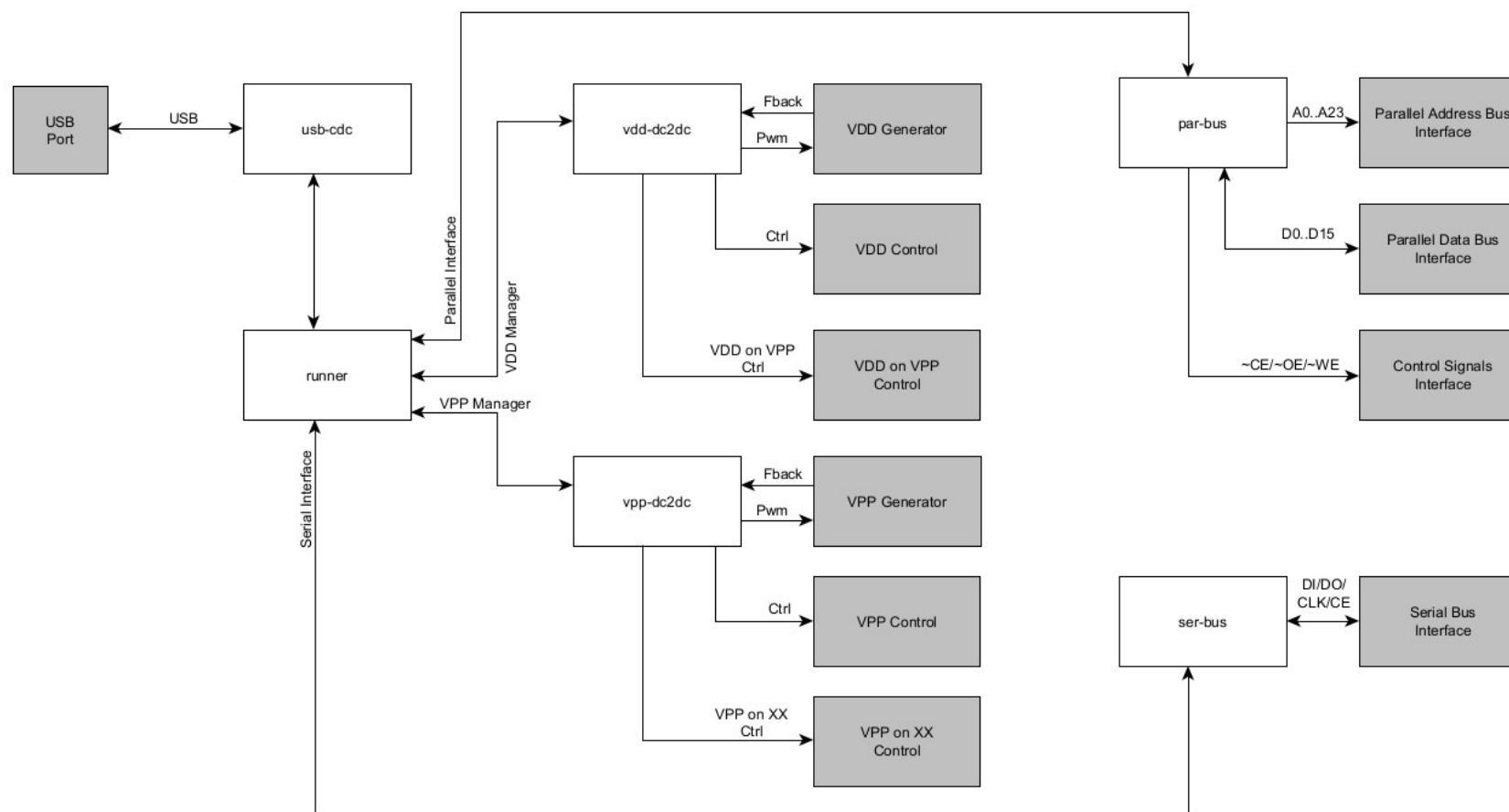
1	3	5	7	9	11	13	15	17	19
2	4	6	8	10	12	14	16	18	20

Table 2: Serial Adapter Connector Pin-Out

Pin	Function	Description
1	VPP13	VPP PROGRAMMING VOLTAGE (13V)
2	VPP13	VPP PROGRAMMING VOLTAGE (13V)
3	VDD5	VDD VOLTAGE (5V)
4	VDD5	VDD VOLTAGE (5V)
5	GND	GROUND
6	GND	GROUND
7	SCK	SERIAL CLOCK
8	SCK	SERIAL CLOCK
9	GND	GROUND
10	GND	GROUND
11	SDO	SERIAL DATA OUT (TO TARGET SDI)
12	SDI	SERIAL DATA IN (FROM TARGET SDO)
13	GND	GROUND
14	GND	GROUND
15	VCC	VCC SUPPLY (5V – ALWAYS ON)
16	VCC	VCC SUPPLY (5V – ALWAYS ON)
17	\overline{WE}	CHIP SELECT (\overline{WE} PROGRAMMER PIN)
18	\overline{WE}	CHIP SELECT (\overline{WE} PROGRAMMER PIN)
19	GND	GROUND
20	KEY	KEY TO AVOID CONNECTOR INVERSION

4. Firmware Project

4.1. Block Diagram



USB Flash/EPROM Programmer

Firmware Block Diagram

Figure 2: USB Flash/EPROM Programmer Firmware Block Diagram

4.2. Communication Protocol (Opcodes)

For communication between the programmer's hardware and the PC, the following protocol must be used (via USB-CDC serial class).

4.2.1. Response Codes

Table 3: Communication Protocol – Response Codes

Op Code	Mnemonic	Description
0x00	CMD RESPONSE NOK	Response NOK.
0x01	CMD RESPONSE OK	Response OK.

4.2.2. Command Codes

Table 4: Communication Protocol – Command Codes (Low Level)

Op Code	Mnemonic	Parameters	Response	Description
Low Level Commands				
0x00	NOP	<none>	OK	No Operation.
0x01	CMD VDD CTRL	STATE	OK NOK	Set VDD Ctrl Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x02	CMD VDD SETV	VALUE	OK NOK	Set VDD Voltage. Parameter VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x03	CMD VDD GETV	<none>	OK + VALUE NOK	Get VDD Voltage. Response VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x04	CMD VDD GET%	<none>	OK + VALUE NOK	Get VDD PWM Duty Cycle (%). Response VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x05	CMD VDD GETCAL	<none>	OK + VALUE NOK	Get VDD Calibration Value. Response VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x06	CMD VDD INITCAL	<none>	OK NOK	Init VDD Calibration Process.
0x07	CMD VDD SAVECAL	VALUE	OK NOK	Save VDD Calibration Value. Parameter VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value

Op Code	Mnemonic	Parameters	Response	Description
0x08	CMD VDD ON VPP	STATE	OK NOK	Set VDD On VPP Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x11	CMD VPP CTRL	STATE	OK NOK	Set VPP Ctrl Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x12	CMD VPP SETV	VALUE	OK NOK	Set VPP Voltage. Parameter VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x13	CMD VPP GETV	<none>	OK + VALUE NOK	Get VPP Voltage. Response VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x14	CMD VPP GET%	<none>	OK + VALUE NOK	Get VPP PWM Duty Cycle (%). Response VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x15	CMD VPP GETCAL	<none>	OK + VALUE NOK	Get VPP Calibration Value. Response VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x16	CMD VPP INITCAL	<none>	OK NOK	Init VPP Calibration Process.
0x17	CMD VPP SAVECAL	VALUE	OK NOK	Save VPP Calibration Value. Parameter VALUE is two byte size. FIRST = Integer part of value SECOND = Fractional part of value
0x18	CMD VPP ON A9	STATE	OK NOK	Set VPP On A9 Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x19	CMD VPP ON A18	STATE	OK NOK	Set VPP On A18 Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x1A	CMD VPP ON CE	STATE	OK NOK	Set VPP On CE Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x1B	CMD VPP ON OE	STATE	OK NOK	Set VPP On OE Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x1C	CMD VPP ON WE	STATE	OK NOK	Set VPP On WE Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.

Op Code	Mnemonic	Parameters	Response	Description
0x21	CMD BUS CE CTRL	STATE	OK NOK	Set CE Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x22	CMD BUS OE CTRL	STATE	OK NOK	Set OE Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x23	CMD BUS WE CTRL	STATE	OK NOK	Set WE Pin On or Off. Parameter STATE is one byte size. If STATE == 0x00, will be OFF; If STATE != 0x00, will be ON.
0x31	CMD BUS AD CLR	<none>	OK NOK	Clear Address Bus Value (Set Address to 0x00).
0x32	CMD BUS AD INC	<none>	OK NOK	Increment Address Bus Value.
0x33	CMD BUS AD SET	VALUE	OK NOK	Set Address Bus Value. Parameter VALUE is three byte size. FIRST = HI SECOND = MID THIRD = LOW
0x34	CMD BUS AD SETB	VALUE	OK NOK	Set Address Bus Value (BYTE). Parameter VALUE is one byte size. VALUE = LOW
0x35	CMD BUS AD SETW	VALUE	OK NOK	Set Address Bus Value (WORD). Parameter VALUE is two byte size. FIRST = MID SECOND = LOW
0x41	CMD BUS DT CLR	<none>	OK NOK	Clear Data Bus Value (Set Data to 0x00).
0x42	CMD BUS DT SET	VALUE	OK NOK	Set Data Bus Value. Parameter VALUE is two byte size. FIRST = HI SECOND = LOW
0x43	CMD BUS DT SETB	VALUE	OK NOK	Set Data Bus Value (BYTE). Parameter VALUE is one byte size. VALUE = LOW
0x44	CMD BUS DT GET	<none>	OK + VALUE NOK	Get Data Bus Value. Response VALUE is two byte size. FIRST = HI SECOND = LOW
0x45	CMD BUS DT GETB	<none>	OK + VALUE NOK	Get Data Bus Value (BYTE). Response VALUE is one byte size. VALUE = LOW
TODO	CMD SERIAL BUS			TODO: Serial Bus Commands.

Table 5: Communication Protocol – Command Codes (High Level)

Op Code	Mnemonic	Parameters	Response	Description												
High Level Commands																
0x81	CMD DEVICE SET TWP	VALUE	OK	Set the tWP Value for Programming a Device. Parameter VALUE is four byte size.												
0x82	CMD DEVICE SET TWC	VALUE	OK	Set the tWC Value for Programming a Device. Parameter VALUE is four byte size.												
0x83	CMD DEVICE SET FLAGS	VALUE	OK	Set the Device Flags for Programming a Device. Parameter VALUE is one byte size. <table><tr><th>Bit</th><th>Description</th></tr><tr><td>0</td><td>Skip Write of 0xFF</td></tr><tr><td>1</td><td>Program with VPP on</td></tr><tr><td>2</td><td>VPP/OE pin</td></tr><tr><td>3</td><td>PGM/CE pin</td></tr><tr><td>4</td><td>PGM is positive</td></tr></table>	Bit	Description	0	Skip Write of 0xFF	1	Program with VPP on	2	VPP/OE pin	3	PGM/CE pin	4	PGM is positive
Bit	Description															
0	Skip Write of 0xFF															
1	Program with VPP on															
2	VPP/OE pin															
3	PGM/CE pin															
4	PGM is positive															
0x84	CMD DEVICE READ	<none>	OK + VALUE NOK	Read Data from Device at current address, and Increment the address. Response VALUE is two byte size. FIRST = HI SECOND = LOW												
0x85	CMD DEVICE READB	<none>	OK + VALUE NOK	Read Data (BYTE) from Device at current address, and Increment the address. Response VALUE is one byte size. VALUE = LOW												
0x86	CMD DEVICE WRITE	VALUE	OK NOK	Program Data to Device at current address, and Increment the address. Parameter VALUE is two byte size. FIRST = HI SECOND = LOW												
0x87	CMD DEVICE WRITEB	VALUE	OK NOK	Program Data (BYTE) to Device at current address, and Increment the address. Parameter VALUE is one byte size. VALUE = LOW												
0x88	CMD DEVICE VERIFY	VALUE	OK NOK	Verify Data from Device at current address, and Increment the address. Parameter VALUE is two byte size. FIRST = HI SECOND = LOW												
0x89	CMD DEVICE VERIFYB	VALUE	OK NOK	Verify Data (BYTE) from Device at current address, and Increment the address. Parameter VALUE is one byte size. VALUE = LOW												

5. Software Project

5.1. Device Algorithms

To read, write and erase memory devices, some algorithms are defined in the software. These algorithms are described below.

5.1.1. Parallel Memory – SRAM

Static Random-Access Memory (SRAM) is a type of random-access memory (RAM) that uses latching circuitry (flip-flop) to store each bit. SRAM is volatile memory; data is lost when power is removed.

The most common SRAM chips operate on 5V power supply (VDD), and the same voltage is used for write and erase (VPP).

Common pinouts

Considering most SRAMs encapsulated with DIP packages, the most common pinouts are shown below:

Table 6: SRAM DIP24 – Pinout

xx16 (2K)		Chip	xx16 (2K)	
A7	1		24	VDD
A6	2		23	A8
A5	3		22	A9
A4	4		21	\overline{WE}
A3	5		20	\overline{OE}
A2	6		19	A10
A1	7		18	\overline{CE}
A0	8		17	D7
D0	9		16	D6
D1	10		15	D5
D2	11		14	D4
GND	12		13	D3

Table 7: SRAM DIP28 – Pinout

xx256 (32K)	xx128 (16K)	xx64 (8K)		Chip		xx64 (8K)	xx128 (16K)	xx256 (32K)
A14	NC	NC	1		28	VDD	VDD	VDD
A12	A12	A12	2		27	\overline{WE}	\overline{WE}	\overline{WE}
A7	A7	A7	3		26	NC	A13	A13
A6	A6	A6	4		25	A8	A8	A8
A5	A5	A5	5		24	A9	A9	A9
A4	A4	A4	6		23	A11	A11	A11
A3	A3	A3	7		22	\overline{OE}	\overline{OE}	\overline{OE}
A2	A2	A2	8		21	A10	A10	A10
A1	A1	A1	9		20	\overline{CE}	\overline{CE}	\overline{CE}
A0	A0	A0	10		19	D7	D7	D7
D0	D0	D0	11		18	D6	D6	D6
D1	D1	D1	12		17	D5	D5	D5
D2	D2	D2	13		16	D4	D4	D4
GND	GND	GND	14		15	D3	D3	D3

Read Cycle

The SRAM read cycle can be illustrated:

Read Cycle 1⁽¹⁾

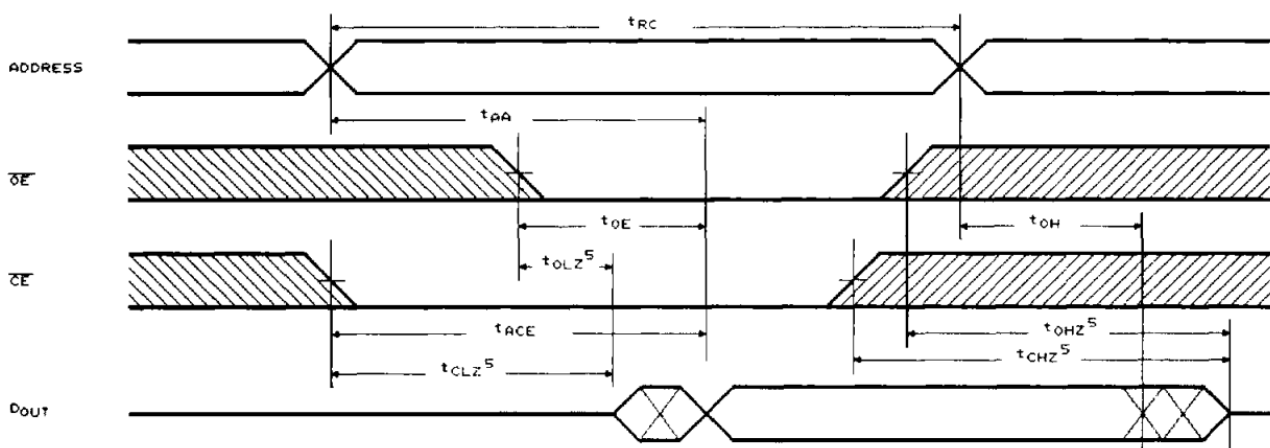


Figure 3: SRAM Read Cycle

To read a SRAM, the following steps are required:

1. Power the SRAM with VDD;
2. Put \overline{WE} , \overline{OE} in HI;
3. Put \overline{CE} in LO;
4. Put the address on bus A0..An;
5. Put \overline{OE} in LO;
6. The data will be available on bus D0..Dn.

Write Cycle

The SRAM write cycle can be illustrated:

Write Cycle 1⁽⁶⁾
(Write Enable Controlled)

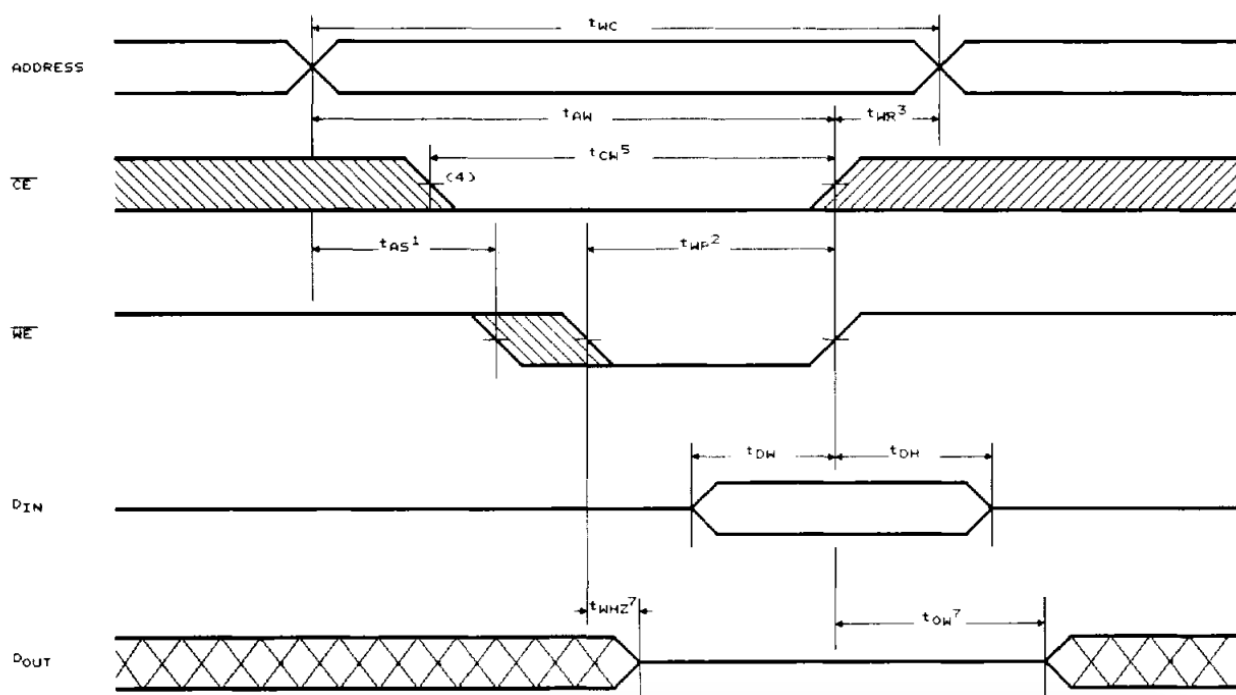


Figure 4: SRAM Write Cycle

To write a SRAM, the following steps are required:

1. Power the SRAM with VDD;
2. Put \overline{WE} , \overline{OE} in HI;
3. Put \overline{CE} in LO;
4. Put the address on bus A0..An;
5. Put the data on bus D0..Dn;
6. Put \overline{WE} in LO;
7. Wait for tWP time;
8. Put \overline{WE} in HI;
9. The data will be recorded in memory.

SRAM Test Algorithm

As SRAM is a volatile memory, it isn't possible to write for later reading, as data is lost when the power is turned off. So, instead, a SRAM memory testing algorithm was proposed, as follows.

SRAM Test Algorithm

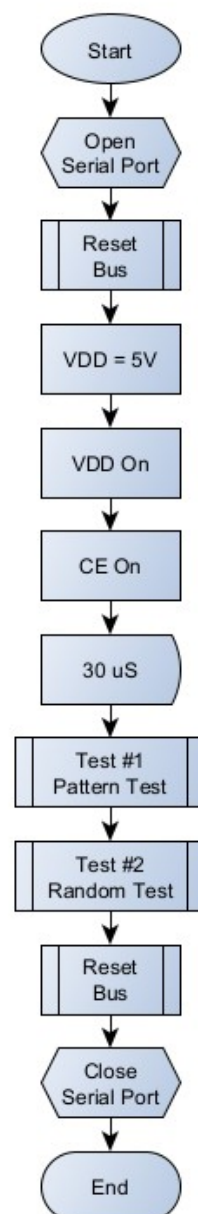


Figure 5: SRAM Test Algorithm

In this algorithm, the memory runs two tests: one is the pattern test, which writes the patterns 01010101 and 10101010 alternately to the memory addresses. The other is the random test, which writes a random number to each memory location. In both tests, the

memory is written and read at each address, being checked, and then it is completely read, from beginning to end, being checked again against the recorded data.

Reset Bus Routine

The Reset Bus routine is illustrated below.

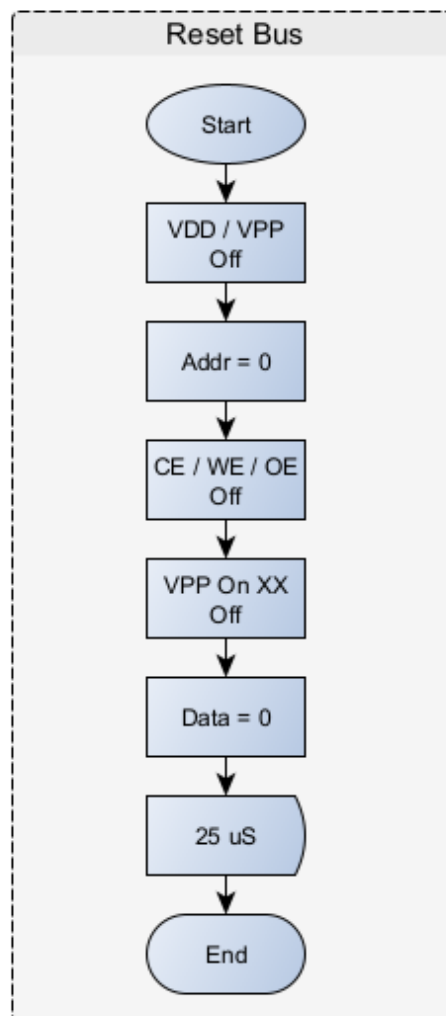


Figure 6: SRAM Reset Bus Routine

This routine is responsible for initializing the buses and pins.

Test #1 Routine

The Test #1 routine is illustrated below.

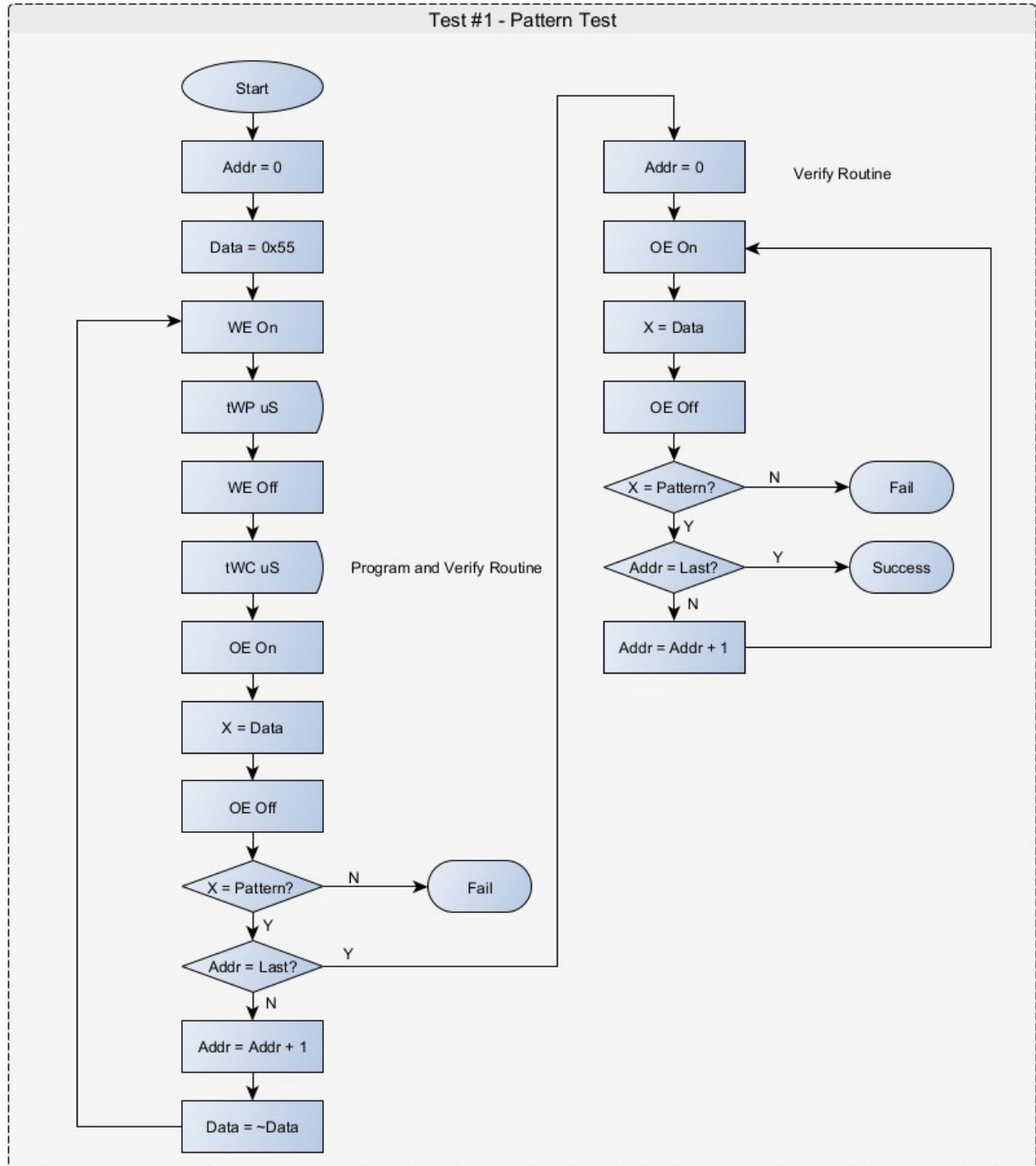


Figure 7: SRAM Pattern Test Routine

This routine is responsible for running the pattern test in memory.

Test #2 Routine

The Test #2 routine is illustrated below.

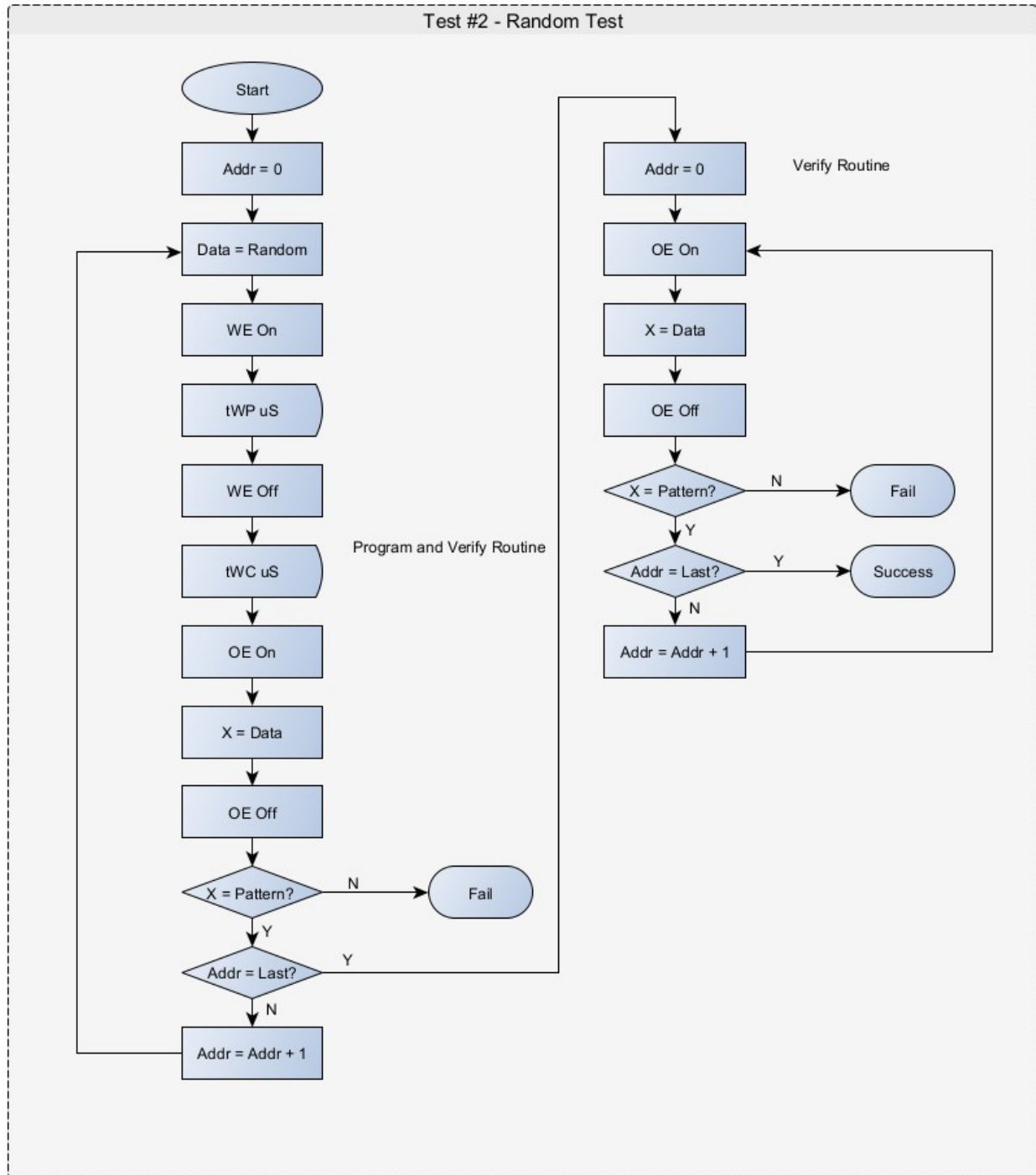


Figure 8: SRAM Random Test Routine

This routine is responsible for running the random test in memory.

5.1.2. Parallel Memory – EPROM

An EPROM, or Erasable Programmable Read-Only Memory, is a type of programmable read-only memory (PROM) chip that retains its data when its power supply is switched off. Computer memory that can retrieve stored data after a power supply has been turned off and back on is called non-volatile. It's an array of floating-gate transistors individually programmed by an electronic device that supplies higher voltages than those normally used in digital circuits. Once programmed, an EPROM can be erased by exposing it to strong ultraviolet (UV) light source (such as from a mercury-vapor lamp).

The most common EPROM chips operate on 5V power supply (VDD) to read, but can use a voltage other than VDD for programming (such as 6V), in addition to a VPP voltage that can vary between 12V and 25V, depending on the model.

Common pinouts

Considering most EPROMs encapsulated with DIP packages, the most common pinouts are shown below:

Table 8: EPROM DIP24 – Pinout

2532 (4K)	27x32 (4K)	27x16 (2K)		Chip		27x16 (2K)	27x32 (4K)	2532 (4K)
A7	A7	A7	1		24	VDD	VDD	VDD
A6	A6	A6	2		23	A8	A8	A8
A5	A5	A5	3		22	A9	A9	A9
A4	A4	A4	4		21	VPP	A11	\overline{OE}/VPP
A3	A3	A3	5		20	\overline{OE}	\overline{OE}/VPP	\overline{CE}/PGM
A2	A2	A2	6		19	A10	A10	A10
A1	A1	A1	7		18	\overline{CE}/PGM	\overline{CE}/PGM	A11
A0	A0	A0	8		17	D7	D7	D7
D0	D0	D0	9		16	D6	D6	D6
D1	D1	D1	10		15	D5	D5	D5
D2	D2	D2	11		14	D4	D4	D4
GND	GND	GND	12		13	D3	D3	D3

Table 9: EPROM DIP28 – Pinout

27x512 (64K)	27x256 (32K)	27x128 (16K)	27x64 (8K)		Chip		27x64 (8K)	27x128 (16K)	27x256 (32K)	27x512 (64K)
A15	VPP	VPP	VPP	1		28	VDD	VDD	VDD	VDD
A12	A12	A12	A12	2		27	$\overline{\text{PGM}}$	$\overline{\text{PGM}}$	A14	A14
A7	A7	A7	A7	3		26	NC	A13	A13	A13
A6	A6	A6	A6	4		25	A8	A8	A8	A8
A5	A5	A5	A5	5		24	A9	A9	A9	A9
A4	A4	A4	A4	6		23	A11	A11	A11	A11
A3	A3	A3	A3	7		22	$\overline{\text{OE}}$	$\overline{\text{OE}}$	$\overline{\text{OE}}$	$\overline{\text{OE}}/\text{VPP}$
A2	A2	A2	A2	8		21	A10	A10	A10	A10
A1	A1	A1	A1	9		20	$\overline{\text{CE}}$	$\overline{\text{CE}}$	$\overline{\text{CE}}/\text{PGM}$	$\overline{\text{CE}}/\text{PGM}$
A0	A0	A0	A0	10		19	D7	D7	D7	D7
D0	D0	D0	D0	11		18	D6	D6	D6	D6
D1	D1	D1	D1	12		17	D5	D5	D5	D5
D2	D2	D2	D2	13		16	D4	D4	D4	D4
GND	GND	GND	GND	14		15	D3	D3	D3	D3

Table 10: EPROM DIP32 – Pinout

27x080 (1M)	27x040 (512K)	27x020 (256K)	27x010 (128K)		Chip		27x010 (128K)	27x020 (256K)	27x040 (512K)	27x080 (1M)
A19	VPP	VPP	VPP	1		32	VDD	VDD	VDD	VDD
A16	A16	A16	A16	2		31	$\overline{\text{PGM}}$	$\overline{\text{PGM}}$	A18	A18
A15	A15	A15	A15	3		30	NC	A17	A17	A17
A12	A12	A12	A12	4		29	A14	A14	A14	A14
A7	A7	A7	A7	5		28	A13	A13	A13	A13
A6	A6	A6	A6	6		27	A8	A8	A8	A8
A5	A5	A5	A5	7		26	A9	A9	A9	A9
A4	A4	A4	A4	8		25	A11	A11	A11	A11
A3	A3	A3	A3	9		24	$\overline{\text{OE}}$	$\overline{\text{OE}}$	$\overline{\text{OE}}$	$\overline{\text{OE}}/\text{VPP}$
A2	A2	A2	A2	10		23	A10	A10	A10	A10
A1	A1	A1	A1	11		22	$\overline{\text{CE}}$	$\overline{\text{CE}}$	$\overline{\text{CE}}/\text{PGM}$	$\overline{\text{CE}}/\text{PGM}$
A0	A0	A0	A0	12		21	D7	D7	D7	D7
D0	D0	D0	D0	13		20	D6	D6	D6	D6
D1	D1	D1	D1	14		19	D5	D5	D5	D5
D2	D2	D2	D2	15		18	D4	D4	D4	D4
GND	GND	GND	GND	16		17	D3	D3	D3	D3

Table 11: EPROM (16Bit) DIP40 – Pinout

27x4096 (512K)	27x2048 (256K)	27x1024 (128K)		Chip		27x1024 (128K)	27x2048 (256K)	27x4096 (512K)
VPP	VPP	VPP	1		40	VDD	VDD	VDD
$\overline{\text{CE}}/\text{PGM}$	$\overline{\text{CE}}$	$\overline{\text{CE}}$	2		39	$\overline{\text{PGM}}$	$\overline{\text{PGM}}$	A17
D15	D15	D15	3		38	NC	A16	A16
D14	D14	D14	4		37	A15	A15	A15
D13	D13	D13	5		36	A14	A14	A14
D12	D12	D12	6		35	A13	A13	A13
D11	D11	D11	7		34	A12	A12	A12
D10	D10	D10	8		33	A11	A11	A11
D9	D9	D9	9		32	A10	A10	A10
D8	D8	D8	10		31	A9	A9	A9
GND	GND	GND	11		30	GND	GND	GND
D7	D7	D7	12		29	A8	A8	A8
D6	D6	D6	13		28	A7	A7	A7
D5	D5	D5	14		27	A6	A6	A6
D4	D4	D4	15		26	A5	A5	A5
D3	D3	D3	16		25	A4	A4	A4
D2	D2	D2	17		24	A3	A3	A3
D1	D1	D1	18		23	A2	A2	A2
D0	D0	D0	19		22	A1	A1	A1
$\overline{\text{OE}}$	$\overline{\text{OE}}$	$\overline{\text{OE}}$	20		21	A0	A0	A0

Table 12: EPROM (16Bit) DIP42 – Pinout

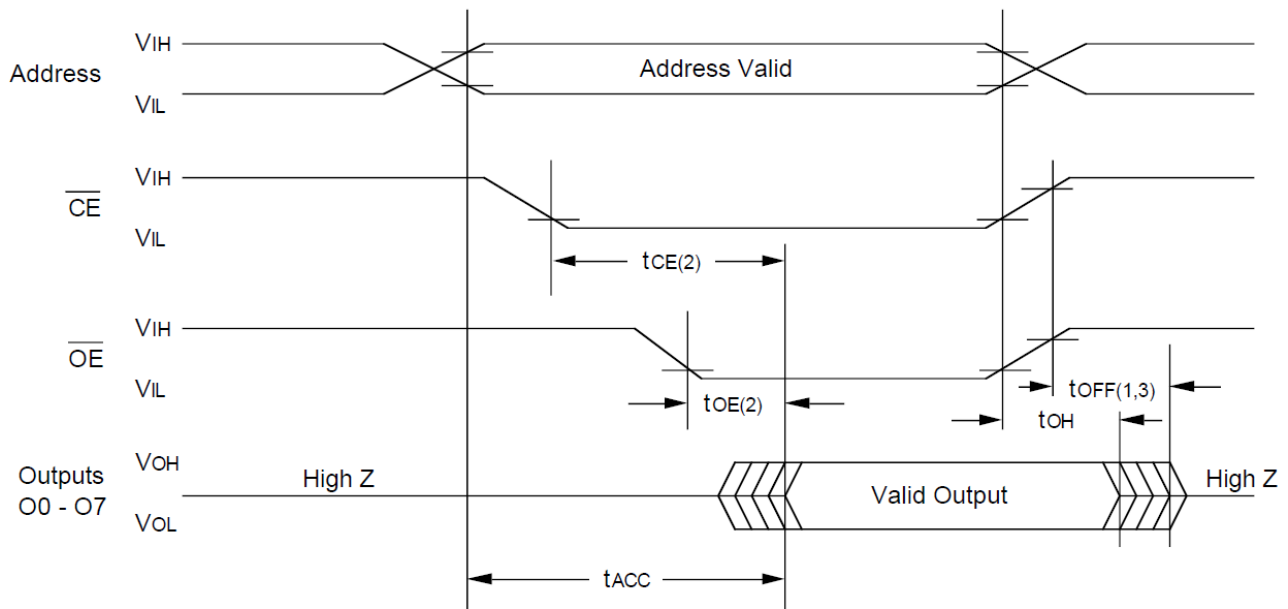
27x320 (4M)	27x160 (2M)	27x800 (1M)	27x400 (512K)		Chip		27x400 (512K)	27x800 (1M)	27x160 (2M)	27x320 (4M)
A18	A18	A18	DIP40	1		42	DIP40	NC	A19	A19
A17	A17	A17	A17	2		41	40 A8	A8	A8	A8
A7	A7	A7	A7	3		40	39 A9	A9	A9	A9
A6	A6	A6	A6	4		39	38 A10	A10	A10	A10
A5	A5	A5	A5	5		38	37 A11	A11	A11	A11
A4	A4	A4	A4	6		37	36 A12	A12	A12	A12
A3	A3	A3	A3	7		36	35 A13	A13	A13	A13
A2	A2	A2	A2	8		35	34 A14	A14	A14	A14
A1	A1	A1	A1	9		34	33 A15	A15	A15	A15
A0	A0	A0	A0	10		33	32 A16	A16	A16	A16
\overline{CE}/PGM	\overline{CE}/PGM	\overline{CE}/PGM	\overline{CE}/PGM	11		32	31 VPP	VPP	VPP	A20
GND	GND	GND	GND	12		31	30 GND	GND	GND	GND
\overline{OE}/VPP	\overline{OE}	\overline{OE}	\overline{OE}	13		30	29 D15	D15	D15	D15
D0	D0	D0	D0	14		29	28 D7	D7	D7	D7
D8	D8	D8	D8	15		28	27 D14	D14	D14	D14
D1	D1	D1	D1	16		27	26 D6	D6	D6	D6
D9	D9	D9	D9	17		26	25 D13	D13	D13	D13
D2	D2	D2	D2	18		25	24 D5	D5	D5	D5
D10	D10	D10	D10	19		24	23 D12	D12	D12	D12
D3	D3	D3	D3	20		23	22 D4	D4	D4	D4
D11	D11	D11	D11	21		22	21 VDD	VDD	VDD	VDD

Notes:

- The $\overline{PGM}/\overline{CE}$ pin is activated by the Programmer using the \overline{WE} pin.
- The \overline{OE}/VPP pin is activated by the Programmer using the VPP pin.
- The \overline{OE} pin is activated by the Programmer using the \overline{OE} pin.
- The \overline{CE} pin is activated by the Programmer using the \overline{CE} pin.

Read Cycle

The EPROM read cycle can be illustrated:



- Notes: (1) t_{OFF} is specified for \overline{OE} or \overline{CE} , whichever occurs first
 (2) \overline{OE} may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of \overline{CE} without impact on t_{CE}
 (3) This parameter is sampled and is not 100% tested.

Figure 9: EPROM Read Cycle

To read an EPROM, the following steps are required:

1. Power the EPROM with VDD (for Read);
2. VPP pin (if any) must be with VDD;
3. \overline{PGM} pin (if any) must be with HI (VDD) – for 27x16, $\overline{CE}/\overline{PGM}$ must be LO;
4. Put \overline{OE} in HI (VDD);
5. Put \overline{CE} in LO;
6. Put the address on bus A0..An;
7. Put \overline{OE} in LO;
8. The data will be available on bus D0..Dn.
9. Put \overline{OE} in HI (VDD);

Program Cycle

The EPROM program cycle can be illustrated:

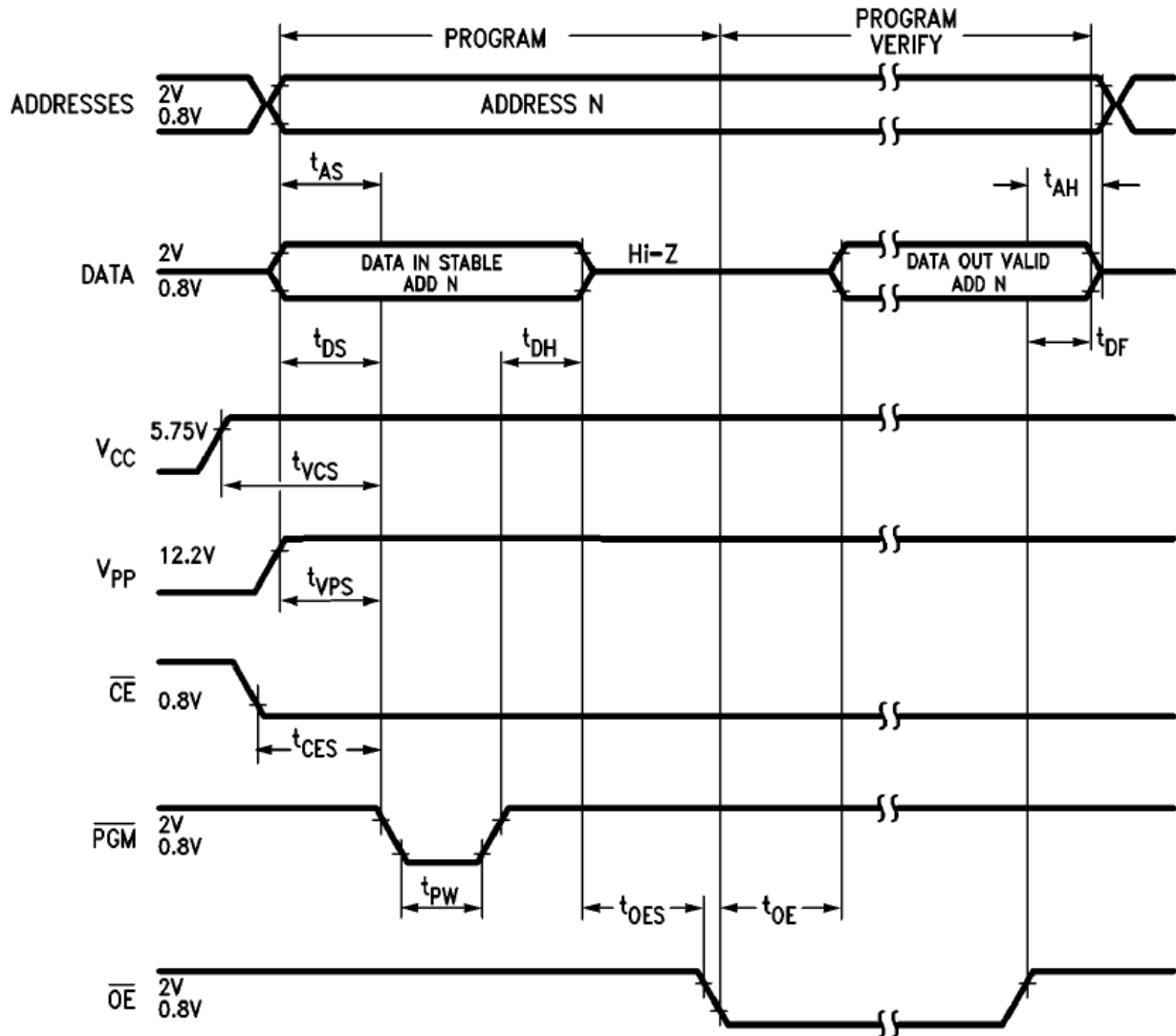


Figure 10: EPROM Program Cycle

To program an EPROM, the following steps are required:

1. Make sure the data is not 0xFF (only zero bits are written);
2. Power the EPROM with VDD (to Program);
3. Put $\overline{\text{PGM}}$, $\overline{\text{OE}}$, $\overline{\text{CE}}$ in HI (VDD) – for 27x16, $\overline{\text{CE}}$ /PGM must be LO;
4. Put $\overline{\text{CE}}$ in LO;
5. Power the EPROM with VPP;
6. Put the address on bus A0..An;
7. Put the data on bus D0..Dn;

8. Put $\overline{\text{PGM}}$ in LO – for 27x16, $\overline{\text{CE}}/\text{PGM}$ must be HI (VDD);
9. Wait for t_{WP} time;
10. Put $\overline{\text{PGM}}$ in HI (VDD) – for 27x16, $\overline{\text{CE}}/\text{PGM}$ must be LO;
11. The data will be recorded in memory;
12. VPP pin (if any) must be with VDD.

To verify data recorded in the same cycle:

1. VPP pin (if any) must be with VDD;
2. $\overline{\text{PGM}}$ pin (if any) must be with HI (VDD) – for 27x16, $\overline{\text{CE}}/\text{PGM}$ must be LO;
3. Put $\overline{\text{OE}}$ in LO;
4. The data will be available on bus D0..Dn;
5. Put $\overline{\text{OE}}$ in HI (VDD).

EPROM Read Algorithm

The EPROM reading algorithm is proposed as follows.

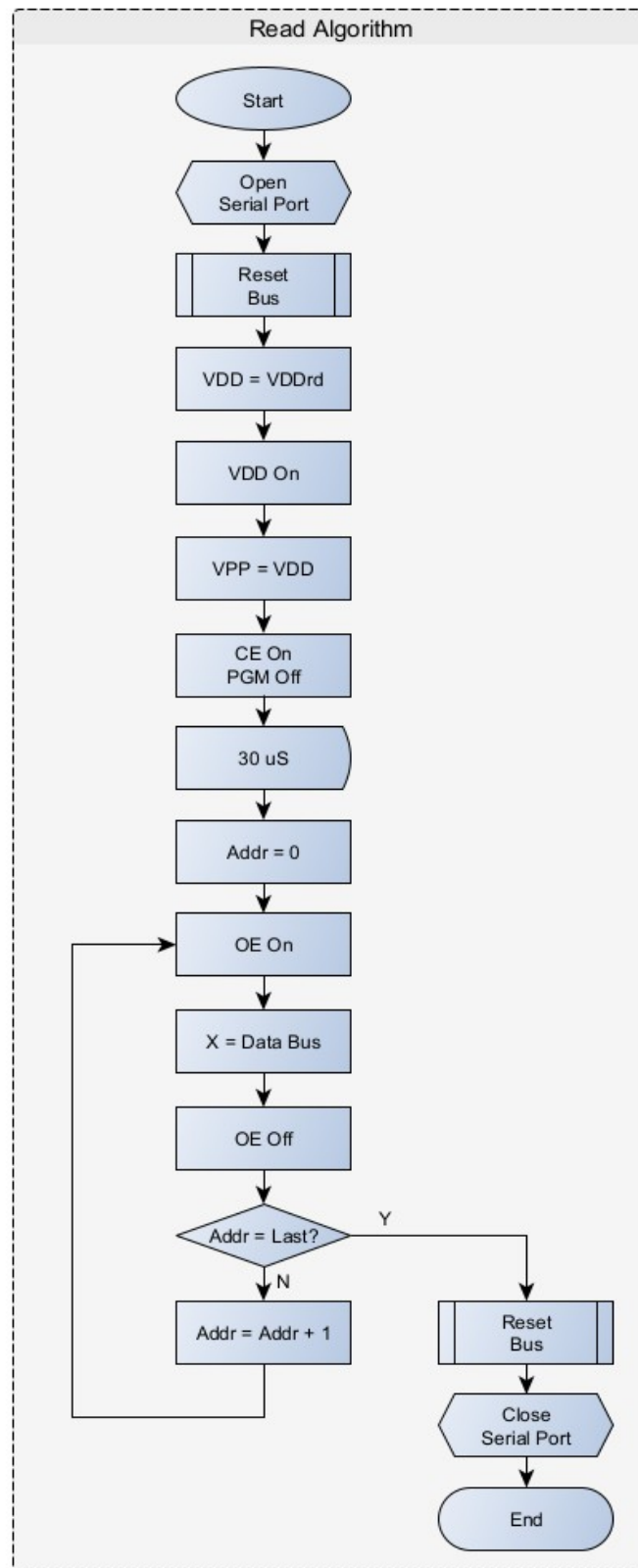


Figure 11: EPROM Read Algorithm

EPROM Program Algorithm

The EPROM programming algorithm is proposed as follows.

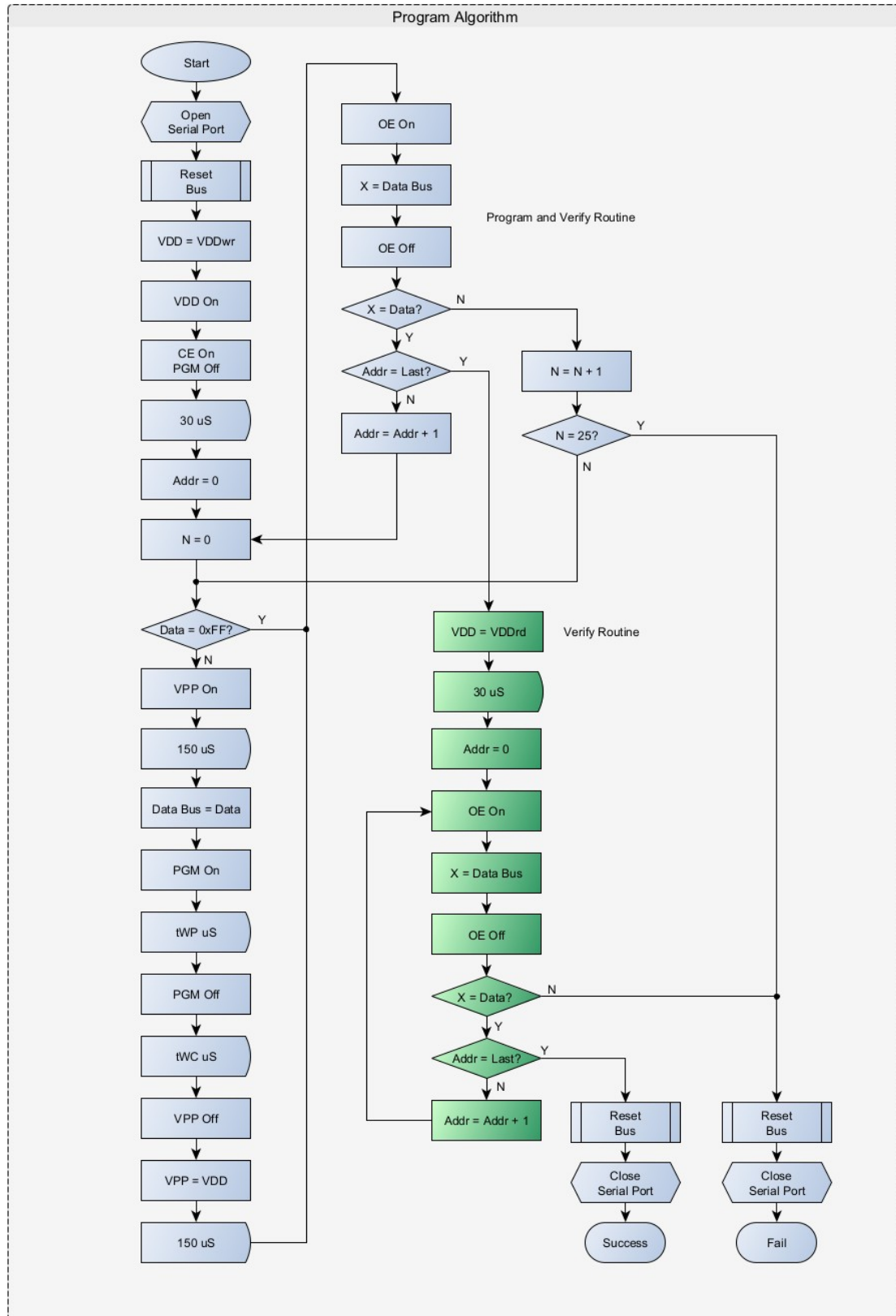


Figure 12: EPROM Program Algorithm

EPROM GetID Algorithm

The EPROM getting ID algorithm is proposed as follows.

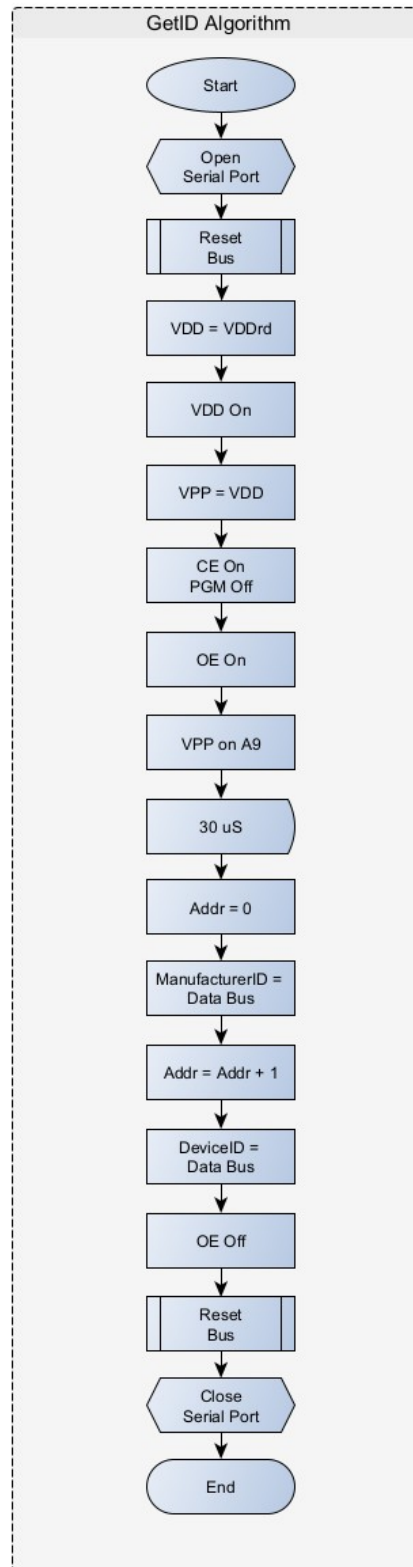


Figure 13: EPROM GetID Algorithm

Reset Bus Routine

The Reset Bus routine is illustrated below.

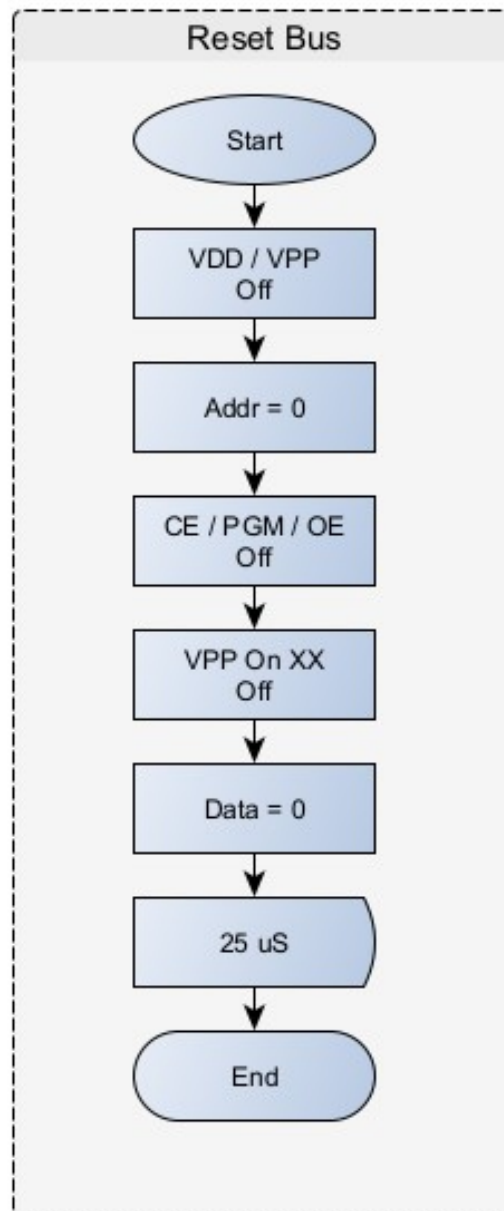


Figure 14: EPROM Reset Bus Routine

5.1.3. Parallel Memory – Electrically Erasable EPROM

An Electrically Erasable EPROM is similar to a conventional CMOS EPROM, but instead of being erased using ultraviolet (UV) light, it can be erased using an electrical pulse.

Common pinouts

The pinouts are the same as conventional EPROMs.

Read Cycle

The reading cycle is the same as conventional EPROMs.

Program Cycle

The programming cycle is the same as conventional EPROMs.

Erase Cycle

The EPROM erase cycle can be illustrated:

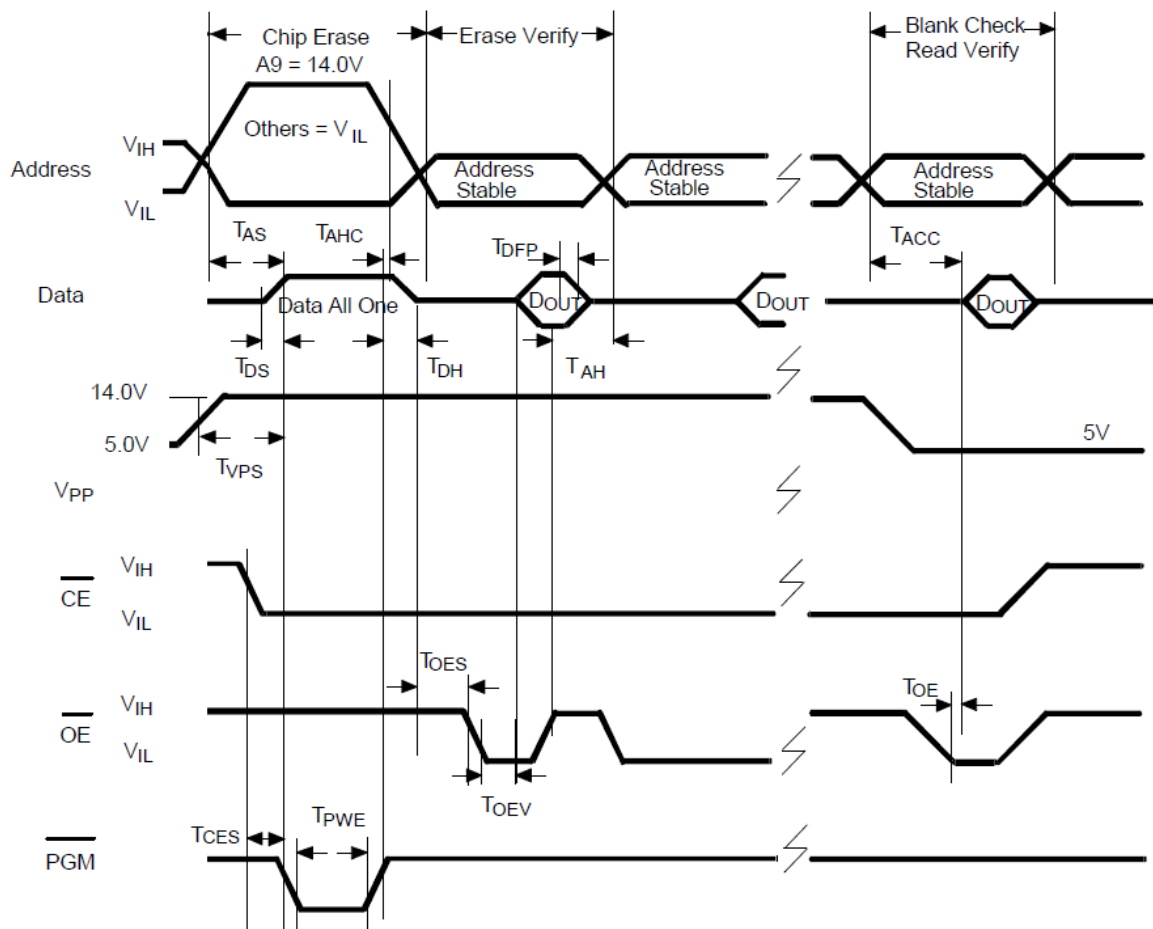


Figure 15: EPROM Erase Cycle

To erase an EPROM, the following steps are required:

1. Power the EPROM with VDD (to Program);
2. Put \overline{PGM} , \overline{OE} , \overline{CE} in HI (VDD);
3. Put the VPP pin with VEE;
4. Put \overline{CE} in LO;
5. Put the address bus with 0x00;
6. Put the A9 pin with VEE;
7. Put the data bus with 0xFF;
8. Put \overline{PGM} in LO;
9. Wait for t_{PWE} time (100 ms);

10. Put $\overline{\text{PGM}}$ in HI (VDD);
11. The all data will be erased.

To verify if data is erased in the same cycle:

1. VPP pin must be with VEE;
2. $\overline{\text{PGM}}$ pin must be with HI (VDD);
3. $\overline{\text{CE}}$ pin must be with LO;
4. Put the address in bus A0..An;
5. Put $\overline{\text{OE}}$ in LO;
6. The data will be available on bus D0..Dn;
7. Put $\overline{\text{OE}}$ in HI (VDD);
8. Check if data is 0xFF. If yes, read the next address (step 4). If no, repeat the erase cycle above (step 5). Do this for up to 20 attempts. If it fails, the device has a problem.

EPROM Read Algorithm

The reading algorithm is the same as conventional EPROMs.

EPROM Program Algorithm

The programming algorithm is the same as conventional EPROMs.

EPROM GetID Algorithm

The getting ID algorithm is the same as conventional EPROMs.

EPROM Erase Algorithm

The EPROM erasing algorithm is proposed as follows.

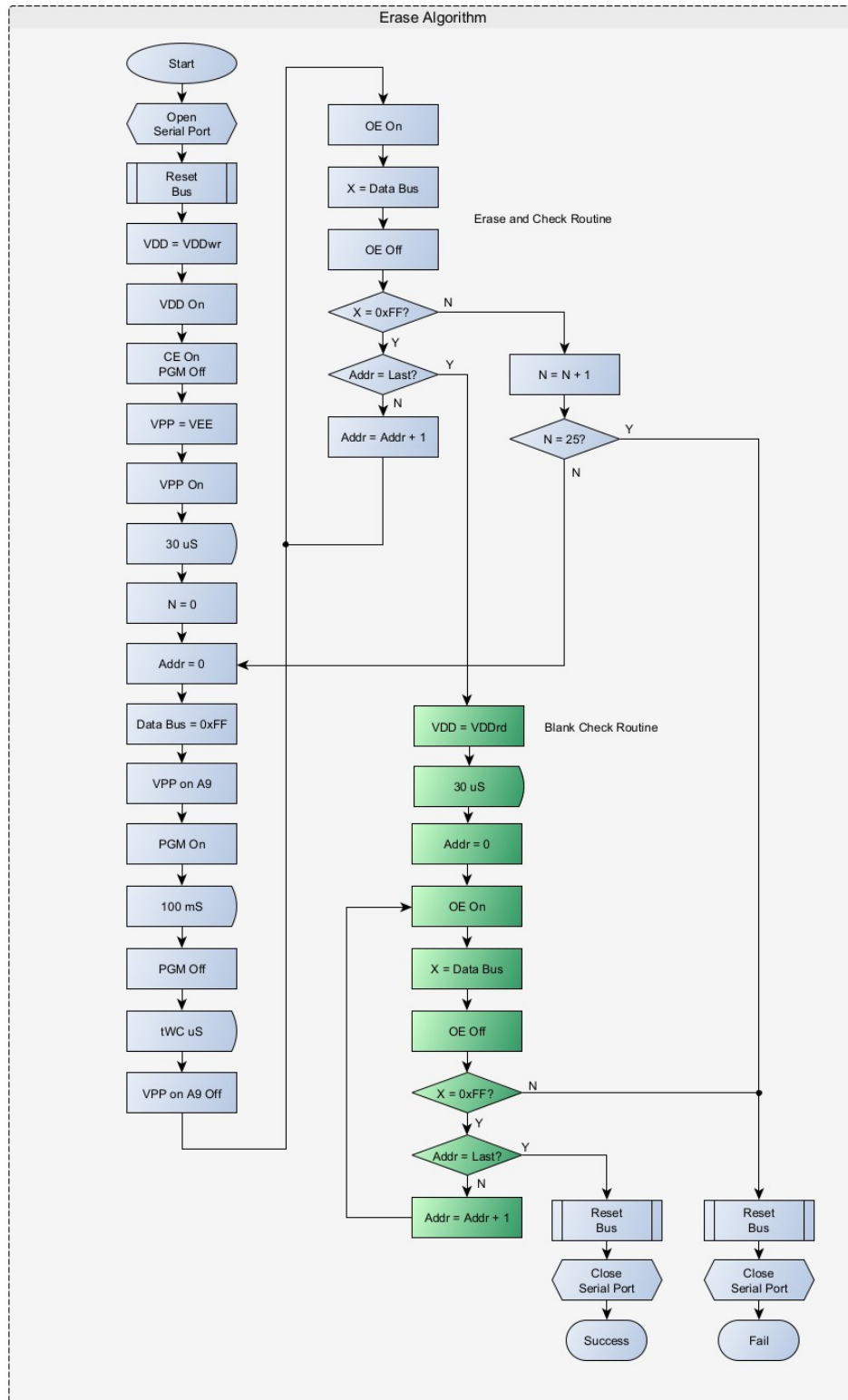


Figure 16: EPROM Erase Algorithm

Appendix A – Development Environment

To develop the programmer, should be used only open source and freeware software:

- **Operating System:**
 - GNU/Linux (<https://distrowatch.com/>)
- **Documentation:**
 - LibreOffice (<https://www.libreoffice.org/>)
 - yEd Graph Editor (<https://www.yworks.com/products/yed>)
- **Hardware Development:**
 - CAD:
 - Kicad (<https://www.kicad.org>)
- **Firmware Development:**
 - Raspberry Pi Pico Module:
 - Raspberry Pi Pico (<https://www.raspberrypi.com/products/raspberry-pi-pico/>)
- **Software Development:**
 - C/C++ Compiler:
 - GCC (<https://gcc.gnu.org/>)
 - GUI Framework:
 - Qt (<https://www.qt.io>)
 - IDE:
 - Qt Creator (<https://www.qt.io/product/development-tools>)
 - Microsoft Visual Studio Code (<https://code.visualstudio.com/>)
 - Code Documentation:
 - Doxygen (<https://www.doxygen.org/>)
- **Version Control System:**
 - Git (<https://git-scm.com/>)